

## MMBTA70

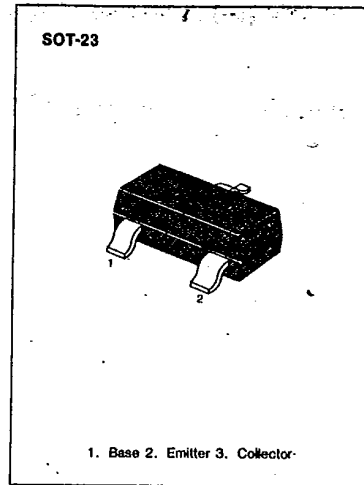
## PNP EPITAXIAL SILICON TRANSISTOR

## AMPLIFIER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CE0}$	40	V
Emitter-Base Voltage	$V_{EBO}$	4	V
Collector Current	$I_C$	100	mA
Collector Dissipation	$P_C$	350	mW
Storage Temperature	$T_{stg}$	150	$^\circ\text{C}$

• Refer to MMBT5086 for graphs

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	$BV_{CE0}$	$I_C = 1.0\text{mA}, I_B = 0$	40		V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	4		V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 30\text{V}, I_E = 0$		100	nA
DC Current Gain	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 5.0\text{mA}$	40	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$		0.25	V
Current Gain-Bandwidth Product	$f_T$	$I_C = 5.0\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$	125		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0$ $f = 100\text{kHz}$		4.0	pF

3

## Marking

